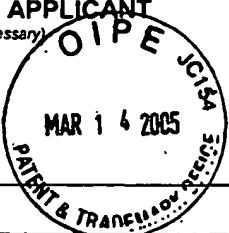


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<b>Filing Date</b>	June 24, 2003
<b>First Named Inventor</b>	Ahn, Kie
<b>Group Art Unit</b>	2823
<b>Examiner Name</b>	Toledo, Fernando

Attorney Docket No: 1303.101US1

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<b>Examiner Name</b>	Toledo, Fernando

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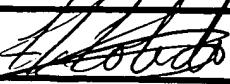
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Examiner Name	Toledo, Fernando

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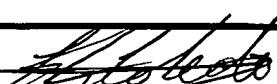
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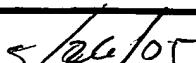
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		Examiner Name	Toledo, Fernando
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		<b>Examiner Name</b>	Toledo, Fernando
Sheet 4 of 5		Attorney Docket No: 1303.101US1	

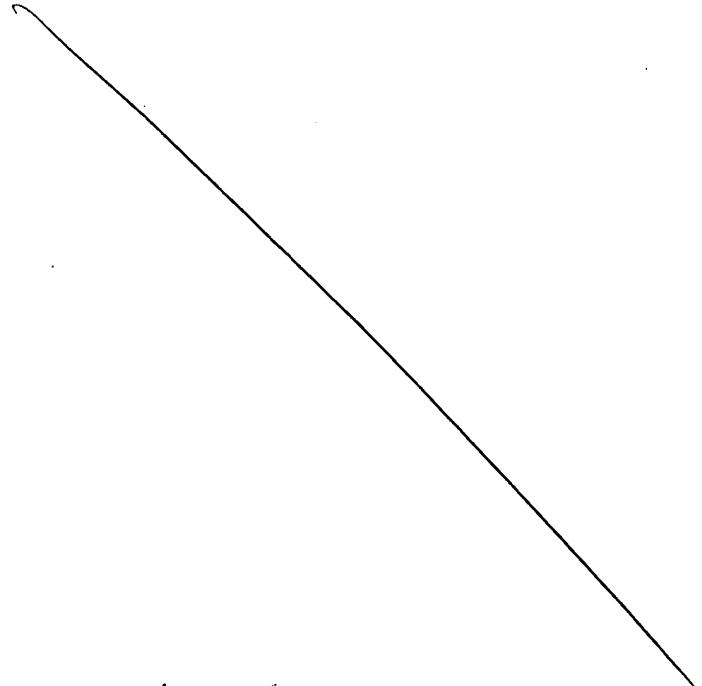
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		Group Art Unit	2812
		Examiner Name	Unknown
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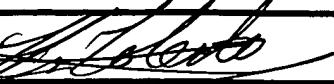
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Substitute Disclosure Statement Form (PTO-1449)

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional) <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached

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